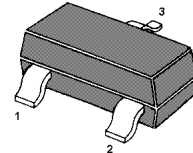
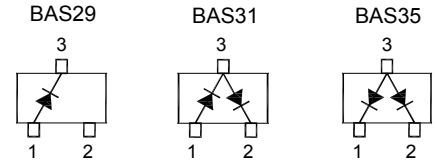




Silicon Epitaxial Planar Switching Diodes

BAS29 Marking Code: L20
 BAS31 Marking Code: L21
 BAS35 Marking Code: L22



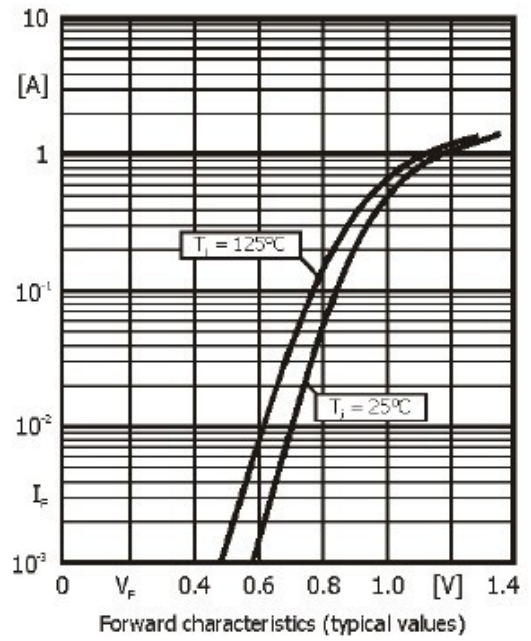
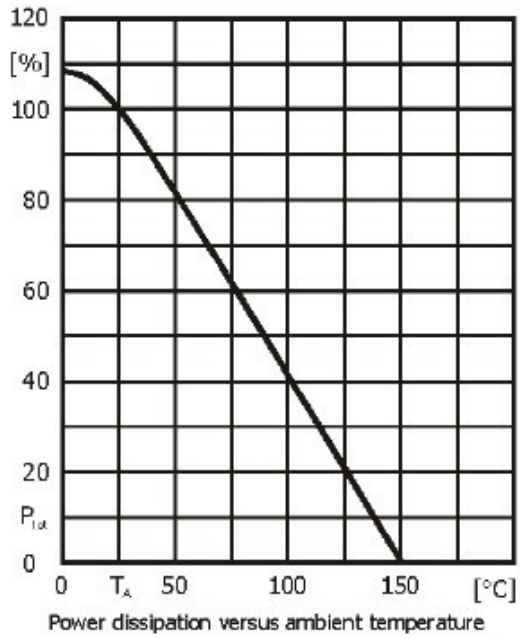
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Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	120	V
Maximum Average Forward Current	I _{F(AV)}	200	mA
Repetitive Peak Forward Current	I _{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	2 1	A
		t = 1 μs t = 1 s	
Power Dissipation	P _{tot}	350	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V _F	-	750	mV
at I _F = 10 mA				
at I _F = 50 mA	V _F	-	840	mV
at I _F = 100 mA	V _F	-	900	mV
at I _F = 200 mA	V _F	-	1	V
at I _F = 400 mA	V _F	-	1.25	V
Reverse Current	I _R	-	100	nA
at V _R = 90 V				
at V _R = 90 V, T _j = 150 °C	I _R	-	100	μA
Reverse Breakdown Voltage	V _{(BR)R}	120	-	V
at I _R = 1 mA				
Total Capacitance	C _T	-	35	pF
at V _R = 0 V, f = 1 MHz				
Reverse Recovery Time	t _{rr}	-	50	ns
at I _F = I _R = 10 mA, I _{tr} = 1 mA, R _L = 100 Ω				





PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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